Silicon Power Transistors

The MJW21195 and MJW21196 utilize Perforated Emitter technology and are specifically designed for high power audio output, disk head positioners and linear applications.

Features

- Total Harmonic Distortion Characterized
- High DC Current Gain $h_{FE} = 20$ Min @ $I_C = 8$ Adc
- Excellent Gain Linearity
- High SOA: 2.25 A, 80 V, 1 Second
- Pb–Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	250	Vdc
Collector-Base Voltage	V _{CBO}	400	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector-Emitter Voltage - 1.5 V	V _{CEX}	400	Vdc
Collector Current – Continuous – Peak (Note 1)	Ι _C	16 30	Adc
Base Current – Continuous	Ι _Β	5.0	Adc
Total Power Dissipation @ T _C = 25°C Derate Above 25°C	P _D	200 1.43	W W/∘C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.7	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

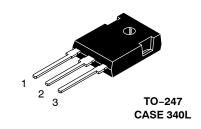
1. Pulse Test: Pulse Width = 5 μ s, Duty Cycle \leq 10%.



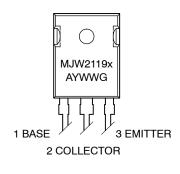
ON Semiconductor®

http://onsemi.com

16 AMPERES COMPLEMENTARY SILICON POWER TRANSISTORS 250 VOLTS, 200 WATTS



MARKING DIAGRAM



= 5 or 6

х

Α

= Assembly Location

Y = Year

- WW = Work Week
- G = Pb-Free Package

ORDERING INFORMATION

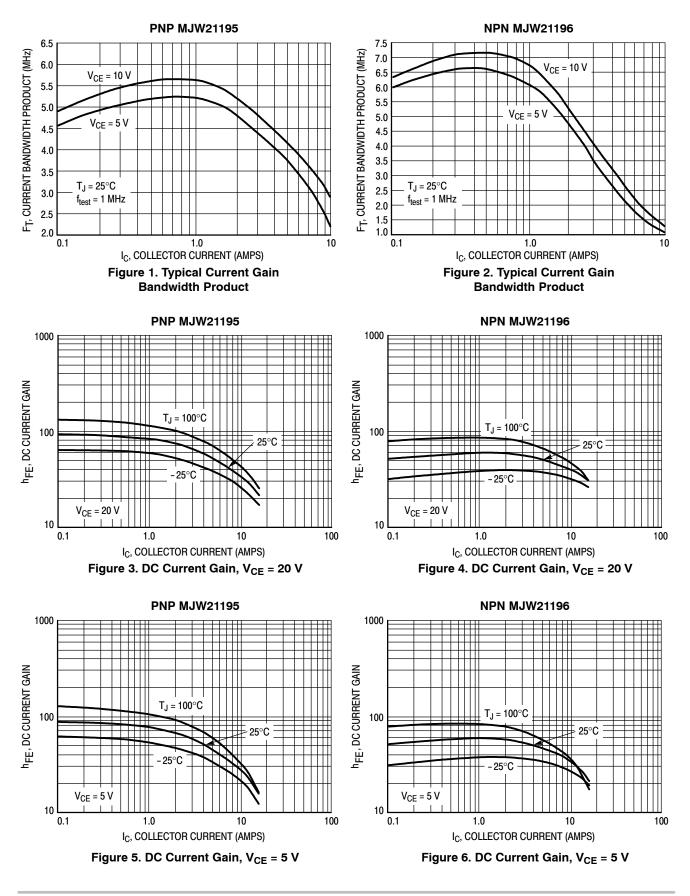
Device	Package	Shipping
MJW21195	TO-247	30 Units/Rail
MJW21195G	TO-247 (Pb-Free)	30 Units/Rail
MJW21196	TO-247	30 Units/Rail
MJW21196G	TO-247 (Pb-Free)	30 Units/Rail

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

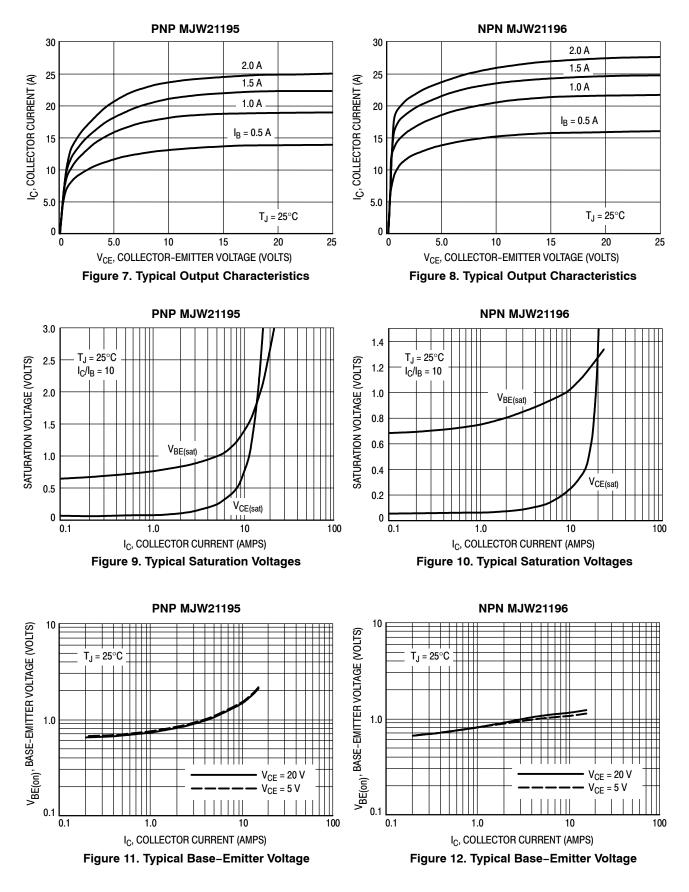
ELECTRICAL CHARACTERISTICS (T_C = 25° C unless otherwise noted)

Characteristic		Symbol	Min	Typical	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Sustaining Voltage ($I_C = 100 \text{ mAdc}, I_B = 0$)		V _{CEO(sus)}	250	-	-	Vdc
Collector Cutoff Current (V _{CE} = 200 Vdc, I _B = 0)		I _{CEO}	-	-	100	μ Adc
Emitter Cutoff Current (V_{CE} = 5 Vdc, I_{C} = 0)		I _{EBO}	-	-	50	μ Adc
Collector Cutoff Current (V _{CE} = 250 Vdc, V _{BE(off)} = 1.5 Vdc)		I _{CEX}	-	-	50	μ Adc
SECOND BREAKDOWN						
Second Breakdown Collector Current with Base Forward Biased $(V_{CE} = 50 \text{ Vdc}, t = 1 \text{ s (non-repetitive)})$ $(V_{CE} = 80 \text{ Vdc}, t = 1 \text{ s (non-repetitive)})$		I _{S/b}	4.0 2.25		-	Adc
ON CHARACTERISTICS						
DC Current Gain ($I_C = 8 \text{ Adc}, V_{CE} = 5 \text{ Vdc}$) ($I_C = 16 \text{ Adc}, I_B = 5 \text{ Adc}$)		h _{FE}	20 8		80 -	
Base-Emitter On Voltage (I _C = 8 Adc, V _{CE} = 5 Vdc)		V _{BE(on)}	-	-	2.0	Vdc
Collector-Emitter Saturation Voltage ($I_C = 8 \text{ Adc}, I_B = 0.8 \text{ Adc}$) ($I_C = 16 \text{ Adc}, I_B = 3.2 \text{ Adc}$)		V _{CE(sat)}			1.0 3	Vdc
DYNAMIC CHARACTERISTICS						
	h _{FE} unmatched	T _{HD}	_	0.8	_	%
(Matched pair h _{FE} = 50 @ 5 A/5 V)	h _{FE} matched		-	0.08	-	
Current Gain Bandwidth Product (I _C = 1 Adc, V _{CE} = 10 Vdc, f _{test} = 1 MHz)		f _T	4	-	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 MHz)		C _{ob}	_	-	500	pF

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS



There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 13 is based on $T_{J(pk)} = 150^{\circ}$ C; T_{C} is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

TYPICAL CHARACTERISTICS

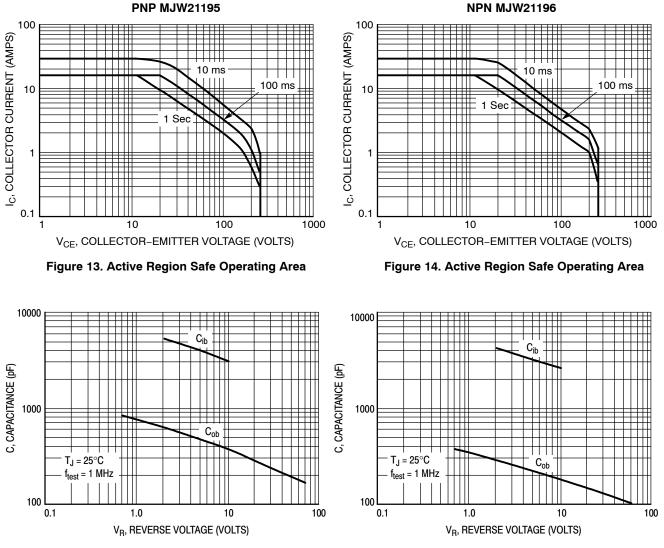


Figure 15. MJW21195 Typical Capacitance

Figure 16. MJW21196 Typical Capacitance

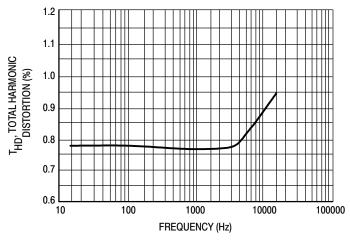


Figure 17. Typical Total Harmonic Distortion

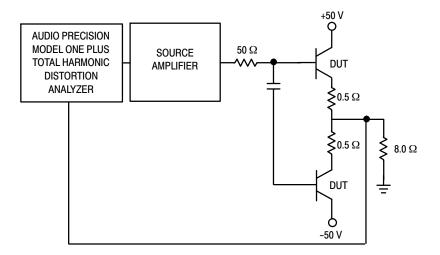
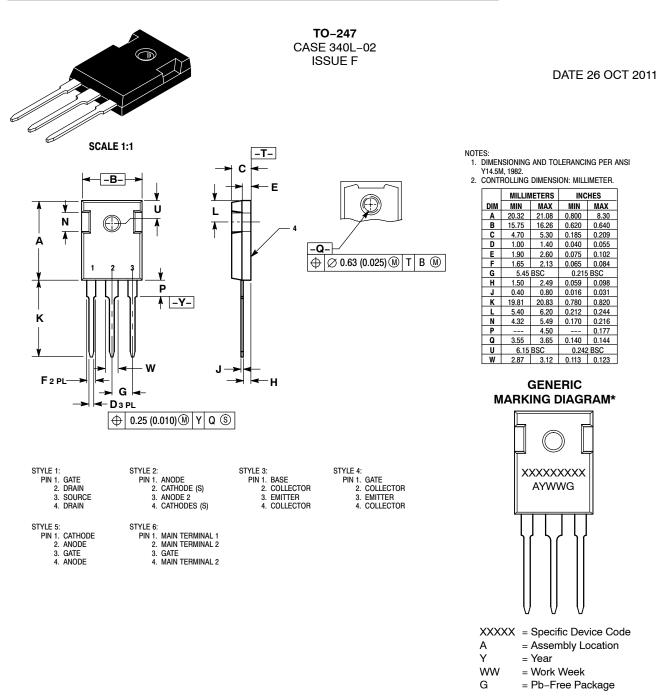


Figure 18. Total Harmonic Distortion Test Circuit

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS





*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present.

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ISSUE	REVISION	DATE
D	CHANGE OF OWNERSHIP FROM MOTOROLA TO ON SEMICONDUCTOR. DIM A WAS 20.80–21.46/0.819–0.845. DIM K WAS 19.81–20.32/0.780–0.800. UPDATED STYLE 1, ADDED STYLES 2, 3, & 4. REQ. BY L. HAYES.	25 AUG 2000
E	DIM E MINIMUM WAS 2.20/0.087. DIM K MINIMUM WAS 20.06/0.790. ADDED GENERIC MARKING DIAGRAM. REQ. BY S. ALLEN.	26 FEB 2010
F	ADDED STYLES 5 AND 6. REQ. BY J. PEREZ.	26 OCT 2011

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